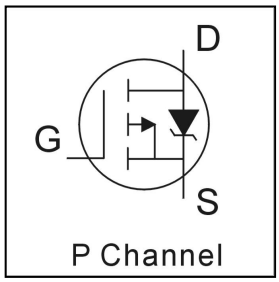
Gunter Semiconductor GmbH | GFC9210

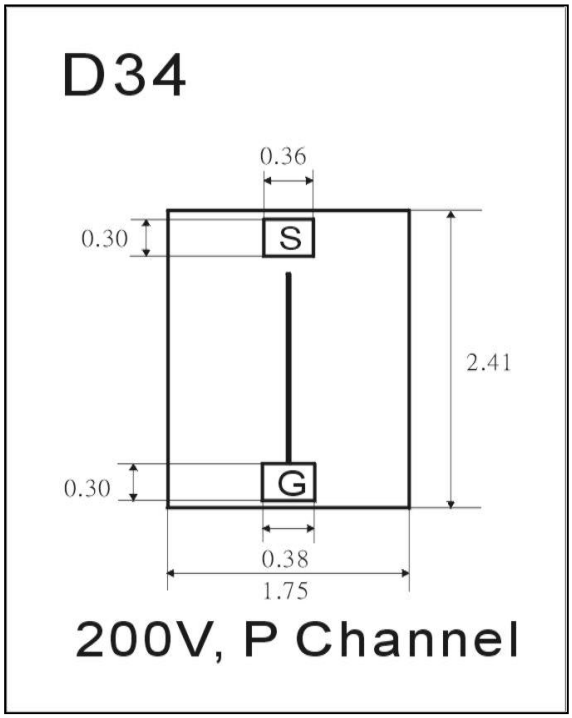
P Channel Power MOSFET



Chip Specification

General Description:

* Advanced Process Technology
* Dynamic dV/dt Rating
* **150℃ Operating Temperature**
* **Fast Switching**
* **Fully Avalanche Rated**



Mechanical Data:

D34	
Dimension	**1.75mm x 2.41mm**
Thickness:	**400 μm**
Metallization**:**	
Top :	: **Al**
Backside :	**CrNiAg / Au**
Suggested Bonding Conditions:	
Die Mounting:	**Solder Perform**
95/5 PbSn or 92.5./2.5/5 PbAgIn	
Source Bonding Wire**:**	**5 mil Al**

Absolute Maximum Rating **@Ta=25℃**

Characteristics	Symbol	Limit	Unit	Test Conditions
Drain-to-Source Breakdown Voltage	-V(BR)DSS	200	V	– VGS=0V, -ID=250μA
Static Drain-to - Source On-resistance	RDS(ON)	3	Ω	– VGS=10V, - ID=0.9A
Continuous Drain current (in target package)	--ID@25℃	1.75	A	- VGS=10V
Continuous Drain current (in target package)	--ID@100℃	1	A	- VGS=10V
Operation Junction Temperatre	Tj	-55~150	℃	
Storage Temperature	TSTR	-55~150	℃	

Target Device: IRF9610

TO-220AB	PD	20	W	@Tc=25℃